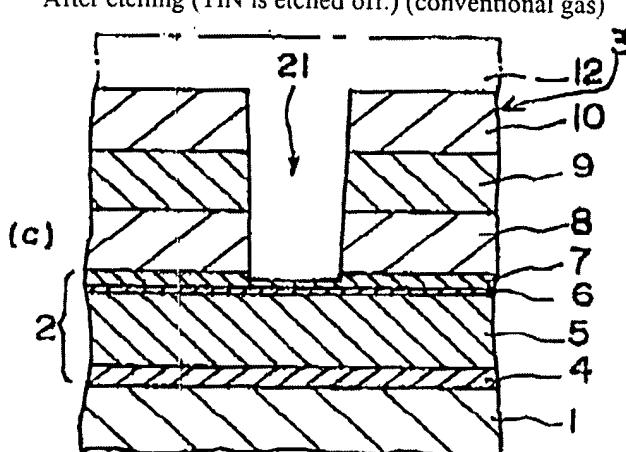
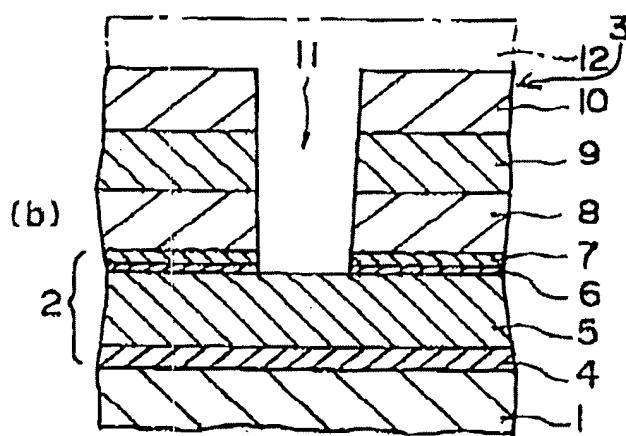
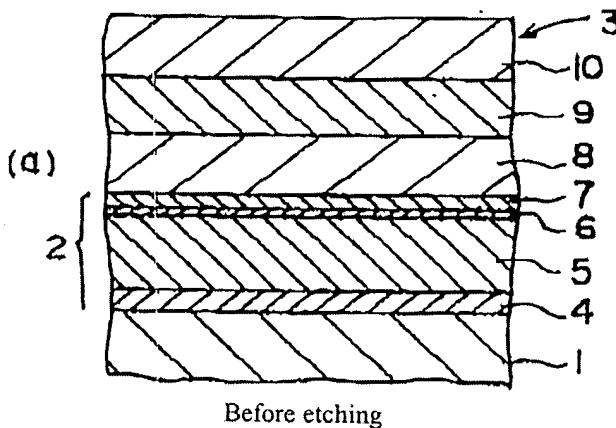
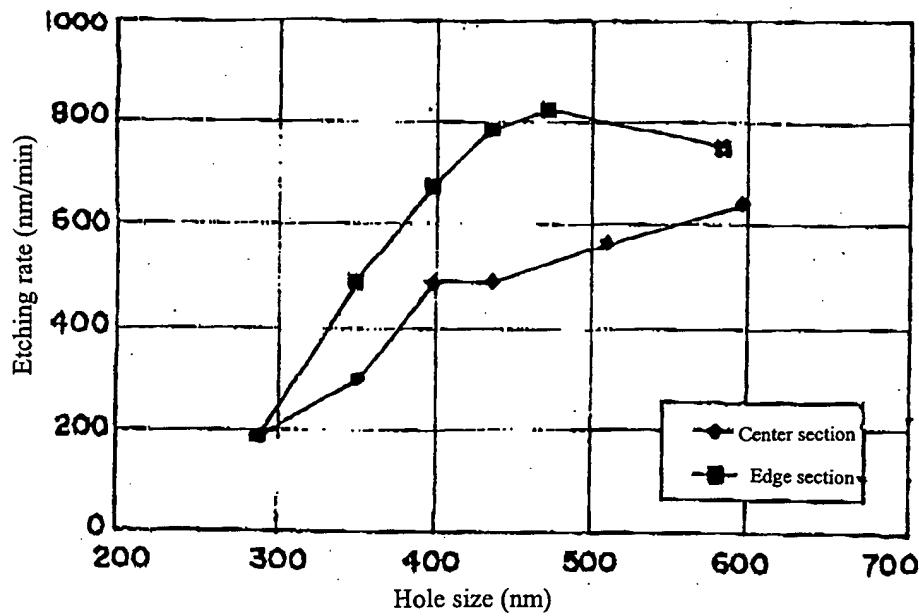


Film constitution of wiring system (thin portion of SOG)

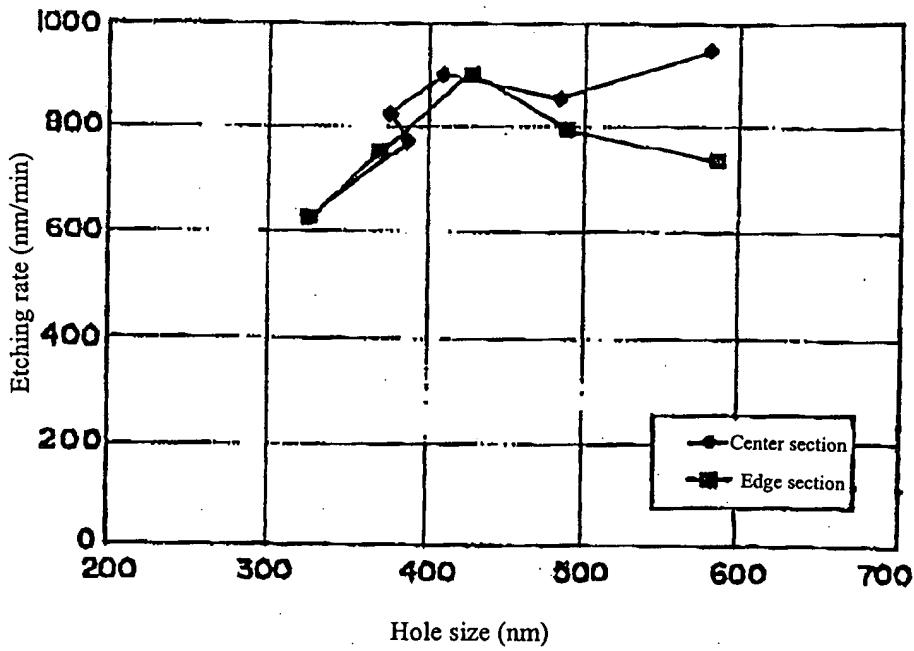
FIG. 1



After etching (etching is stopped by TiN.) (gas of this invention)  
 Film constitution of wiring system (thin portion of SOG)



(a) Conventional conditions



(b) Conditions of this invention

Dependence of SOG etching rate on hole size

FIG. 3

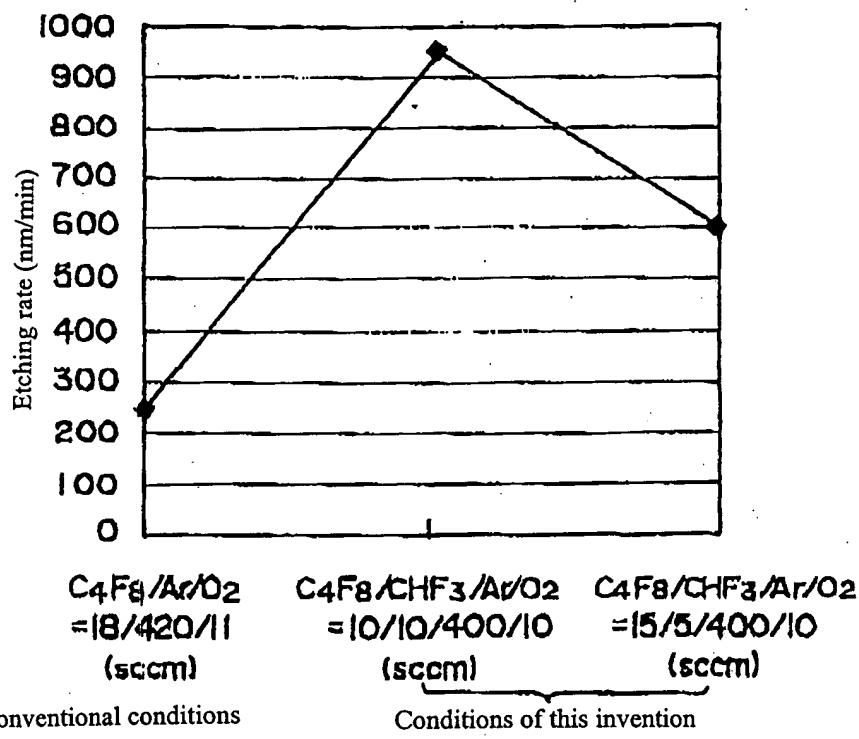
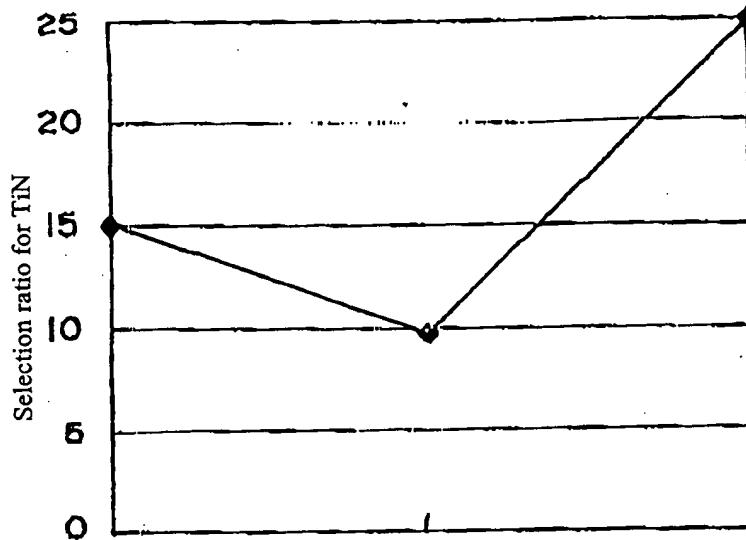


FIG. 4



$$\begin{array}{l} \text{C}_4\text{F}_8/\text{Ar}/\text{O}_2 \\ = 18/420/11 \\ (\text{sccm}) \end{array}$$

C<sub>4</sub>F<sub>8</sub>/CHF<sub>3</sub>/Ar/O<sub>2</sub>    C<sub>4</sub>F<sub>8</sub>/CHF<sub>3</sub>/Ar/O<sub>2</sub>  
 = 10/10/400/10        = 15/5/400/10  
 (sccm)                (sccm)

### Conventional conditions

Conditions of this invention

### Dependence of selection ratio for TiN on gas composition (when hole size is 0.32 $\mu\text{m}$ )

FIG. 5

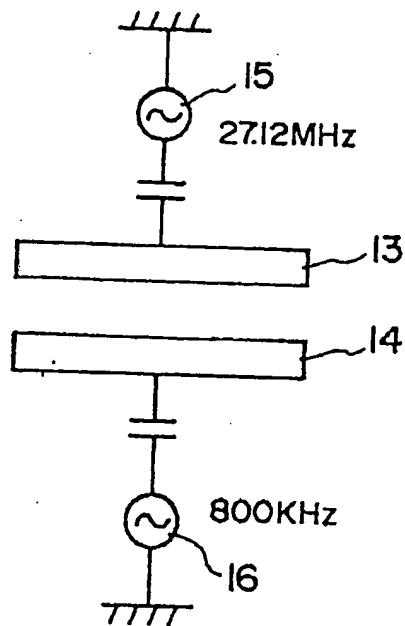


FIG. 6